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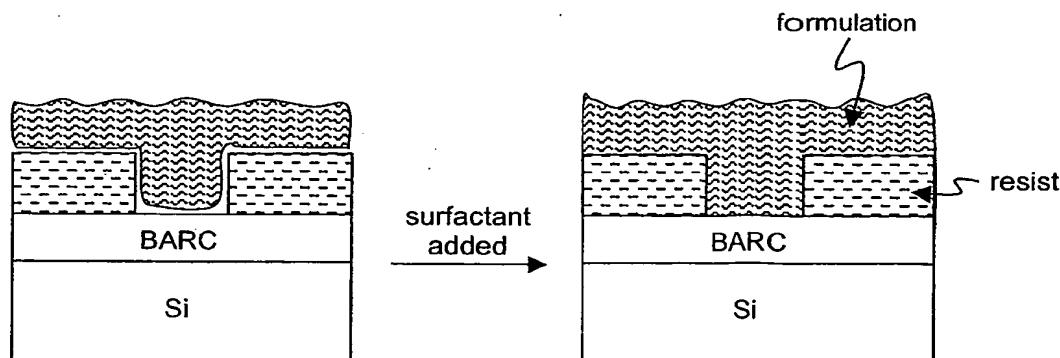
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(54) Title: RESIST, BARC AND GAP FILL MATERIAL STRIPPING CHEMICAL AND METHOD



(57) Abstract: An aqueous-based composition and process for removing photoresist, bottom anti-reflective coating (BARC) material, and/or gap fill material from a substrate having such material(s) thereon. The aqueous-based composition includes a fluoride source, at least one organic amine, at least one organic solvent, water, and optionally chelating agent and/or surfactant. The composition achieves high-efficiency removal of such material(s) in the manufacture of integrated circuitry without adverse effect on metal species on the substrate, such as copper, and without damage to SiOC-based dielectric materials employed in the semiconductor architecture.